

# CITATION REPORT

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## Approaching the Schottky-Mott limit in van der Waals metal-semiconductor junctions

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627	Fe-Ion-Catalyzed Synthesis of CdSe/Cu Core/Shell Nanowires. <b>2021</b> , 60, 2614-2622	4
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273	Interfacial electronic properties of metal/CsSnBr <sub>3</sub> heterojunctions.. <b>2022</b> ,	
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135	Challenges and Opportunities of Chemiresistors Based on Microelectromechanical Systems for Chemical Olfaction.	1
134	P-Type Ohmic Contact to Monolayer WSe <sub>2</sub> Field-Effect Transistors Using High-Electron Affinity Amorphous MoO <sub>3</sub> .	0
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128	Experimental and Modeling Study of Metal-Insulator Interfaces to Control the Electronic Transport in Single Nanowire Memristive Devices.	0
127	Low dark-current V <sub>2</sub> CT x /n-Si van der Waals Schottky photodiode for Hadamard single-pixel imaging. <b>2022</b> , 1-1	1
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110	Wafer-scale integration of transition metal dichalcogenide field-effect transistors using adhesion lithography.	0
109	In Situ Active Switching of Bipolar Current Rectification in 2D Semiconductor Vertical Diodes.	0
108	Controlled synthesis of ultrathin metallic MoO <sub>2</sub> nanosheets for van der Waals contact.	0

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106	Interfacial regulation of aqueous synthesized metal-semiconductor hetero-nanocrystals. 9,	0
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104	Epitaxial van der Waals contacts for low schottky barrier MoS <sub>2</sub> field effect transistors.	0
103	Two/Quasi-two-dimensional Perovskite-based Heterostructures: Construction, Properties and Applications.	0
102	Record-high Work-function p-Type CuBiP <sub>2</sub> Se <sub>6</sub> Atomic Layers for High-photoresponse van der Waals Vertical Heterostructure Phototransistor. 2209995	0
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